

L Number	Hits	Search Text	DB	Time stamp
1	10	duggan adj geoffrey.in.	USPAT	2003/11/05 11:17
2	28	duggan adj geoffrey.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/11/05 11:17
-	1156	((semiconductor near laser) and ((active or gain) near2 (medium or region or layer or film)) and barrier and electron and (clad\$5 near2 (medium or region or layer or film)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/18 12:57
-	93	((semiconductor near laser) and ((active or gain) near2 (medium or region or layer or film)) and barrier and electron and (clad\$5 near2 (medium or region or layer or film))) and reflect\$5 and (potential near2 barrier)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/18 12:48
-	5	((semiconductor near laser) and ((active or gain) near2 (medium or region or layer or film)) and barrier and electron and (clad\$5 near2 (medium or region or layer or film))) and ((electron near3 reflect\$5) WITH (potential near2 barrier))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/18 12:50
-	5	((semiconductor near laser) and ((active or gain) near2 (medium or region or layer or film)) and ((electron near3 reflect\$5) WITH (potential near2 barrier)) and electron and (clad\$5 near2 (medium or region or layer or film)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/18 16:06
-	6	((semiconductor near laser) and ((active or gain) near2 (medium or region or layer or film)) and barrier and electron and (clad\$5 near2 (medium or region or layer or film))) and ((electron near3 reflect\$5) same (potential near2 barrier))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/18 15:59
-	1	((semiconductor near laser) and ((active or gain) near2 (medium or region or layer or film)) and barrier and electron and (clad\$5 near2 (medium or region or layer or film))) and ((electron near3 reflect\$5) same (potential near2 barrier)) not ((semiconductor near laser) and ((active or gain) near2 (medium or region or layer or film)) and ((electron near3 reflect\$5) WITH (potential near2 barrier)) and electron and (clad\$5 near2 (medium or region or layer or film)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/18 15:59
-	6	((semiconductor near laser) and ((active or gain) near2 (medium or region or layer or film)) and ((electron near3 reflect\$5) SAME (potential near2 barrier)) and electron and (clad\$5 near2 (medium or region or layer or film)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/18 16:08
-	24	((semiconductor near laser) and ((active or gain) near2 (medium or region or layer or film)) and ((electron near3 reflect\$5) AND (potential near2 barrier)) and electron and (clad\$5 near2 (medium or region or layer or film)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/18 16:54
-	18	((semiconductor near laser) and ((active or gain) near2 (medium or region or layer or film)) and ((electron near3 reflect\$5) AND (potential near2 barrier)) and electron and (clad\$5 near2 (medium or region or layer or film))) not ((semiconductor near laser) and ((active or gain) near2 (medium or region or layer or film)) and ((electron near3 reflect\$5) SAME (potential near2 barrier)) and electron and (clad\$5 near2 (medium or region or layer or film)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/18 16:29

-	10	(semiconductor near laser) and ((active or gain) near2 (medium or region or layer or film)) and ((electron WITH reflect\$5) WITH (potential near3 barrier)) and electron and (clad\$5 near2 (medium or region or layer or film))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/18 16:54
-	26	(semiconductor near laser) and ((active or gain) near2 (medium or region or layer or film)) and ((electron near5 reflect\$5) AND (potential near2 barrier)) and electron and (clad\$5 near2 (medium or region or layer or film))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/18 16:58
-	7	(semiconductor near laser) and ((active or gain) near2 (medium or region or layer or film)) and ((electron near5 reflect\$5) with (potential near2 barrier)) and electron and (clad\$5 near2 (medium or region or layer or film))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/18 17:03
-	8	(semiconductor near laser) and ((active or gain) near2 (medium or region or layer or film)) and ((electron NEAR5 reflect\$5) WITH (potential\$5 near3 barrier)) and electron and (clad\$5 near2 (medium or region or layer or film))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/19 07:57
-	2	("5425041").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/19 07:55
-	2	(semiconductor near laser) and ((strain or strees or tension) with (electron NEAR5 reflect\$5))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/19 08:01
-	2	("5251224").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/19 08:01
-	19	(semiconductor near laser) and ((active or gain) near2 (medium or region or layer or film)) and ((electron NEAR "5" reflect\$5) WITH (potential near3 barrier)) and electron and (clad\$5 near2 (medium or region or layer or film))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/02 09:35
-	8	(semiconductor near laser) and ((active or gain) near2 (medium or region or layer or film)) and ((electron NEAR5 reflect\$5) WITH (potential near3 barrier)) and electron and (clad\$5 near2 (medium or region or layer or film))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/02 09:36
-	8	(semiconductor near laser) and ((active or gain) near2 (medium or region or layer or film)) and ((electron NEAR5 reflect\$5) WITH (potential near3 barrier)) and electron and (clad\$5 near2 (medium or region or layer or film))	USPAT; EPO; JPO; DERWENT	2003/06/02 09:36
-	8	(semiconductor near laser) and ((active or gain) near2 (medium or region or layer or film)) and ((electron NEAR5 reflect\$5) WITH (potential near3 barrier)) and electron and (clad\$5 near2 (medium or region or layer or film))	USPAT	2003/06/12 10:59
-	6	(semiconductor near laser) and ((active or gain) near2 (medium or region or layer or film)) and ((electron NEAR reflect\$9) WITH (potential near3 barrier)) and electron and (clad\$5 near2 (medium or region or layer or film))	USPAT	2003/06/02 10:21

-	1	("5509024").PN.	USPAT	2003/06/11 13:56
-	8	(semiconductor near laser) and ((active or gain) near2 (medium or region or layer or film)) and ((electron NEAR5 reflect\$5) WITH (potential near3 barrier)) and (clad\$5 near2 (medium or region or layer or film))	USPAT	2003/11/03 10:43
-	178	semiconductor and (active near (layer or region)) and (clad\$5 near (layer or region)) and (electron near3 barrier)	USPAT	2003/10/10 10:13
-	31	(semiconductor near laser) and (active or gain) AND ((electron NEAR5 reflect\$5) WITH barrier) and (clad\$5)	USPAT	2003/11/05 10:29